

Supporting Information

Exploration of stable stoichiometries, physical properties and hardness in the Rh-Si system: A first-principles study

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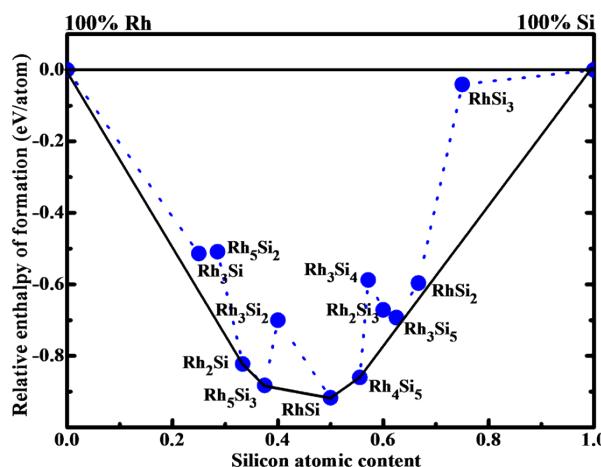


Fig. S1. Relative enthalpies of formation for rhodium silicides. The solid line denotes the ground state convex hull at LDA+U level.

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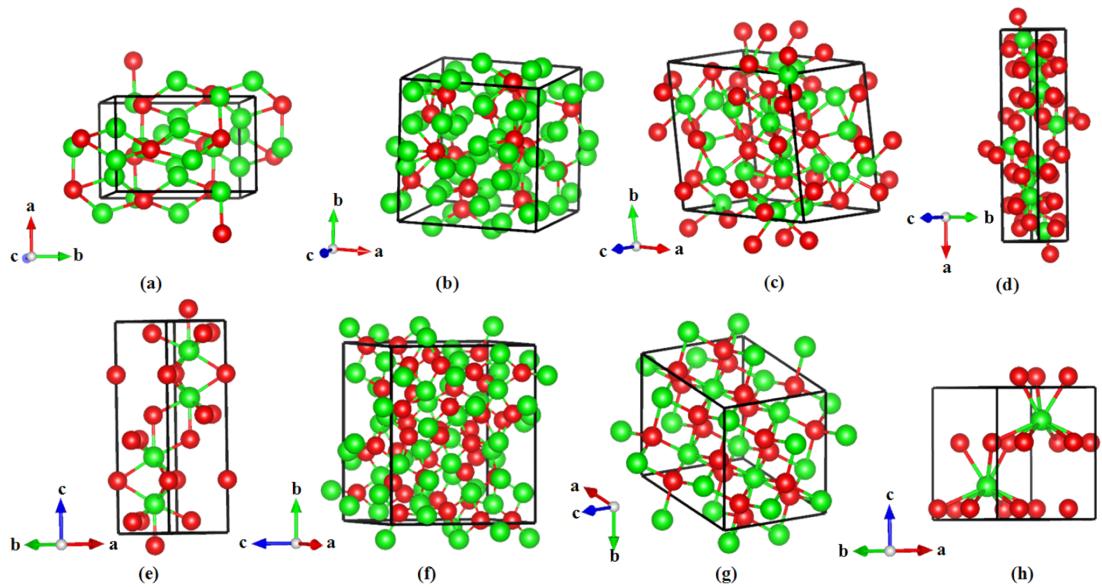


Fig. S2. Optimized structures of rhodium silicides: (a) Rh_3Si ($Pnma$), (b) Rh_5Si_2 ($P4_12_{12}$), (c) Rh_3Si_2 ($Cmc2_1$), (d) Rh_3Si_4 ($Pnma$), (e) Rh_2Si_3 ($P6_3/mmc$), (f) Rh_3Si_5 ($P2_1/c$), (g) RhSi_2 ($Cmce$), (h) RhSi_3 ($P6_3mc$). The green and red spheres represent rhodium and silicon atoms, respectively.

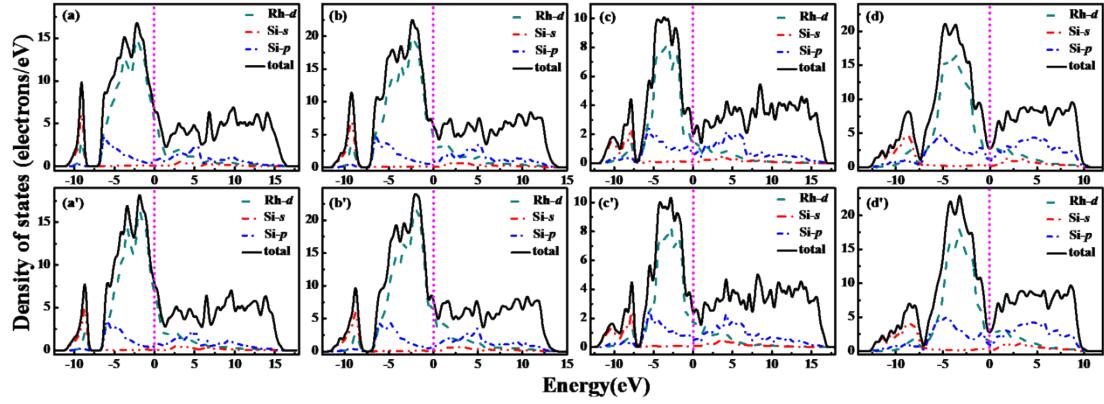


Fig. S3. Calculated total and partial DOSSs of (a) Rh_2Si ($Pnma$), (b) Rh_5Si_3 ($Pbam$), (c) RhSi ($Pnma$), and (d) Rh_4Si_5 ($P2_1/m$) using LDA+U functional, and (a') Rh_2Si ($Pnma$), (b') Rh_5Si_3 ($Pbam$), (c') RhSi ($Pnma$), and (d') Rh_4Si_5 ($P2_1/m$) using GGA-PBE functional, respectively. The Fermi level is at 0 eV.

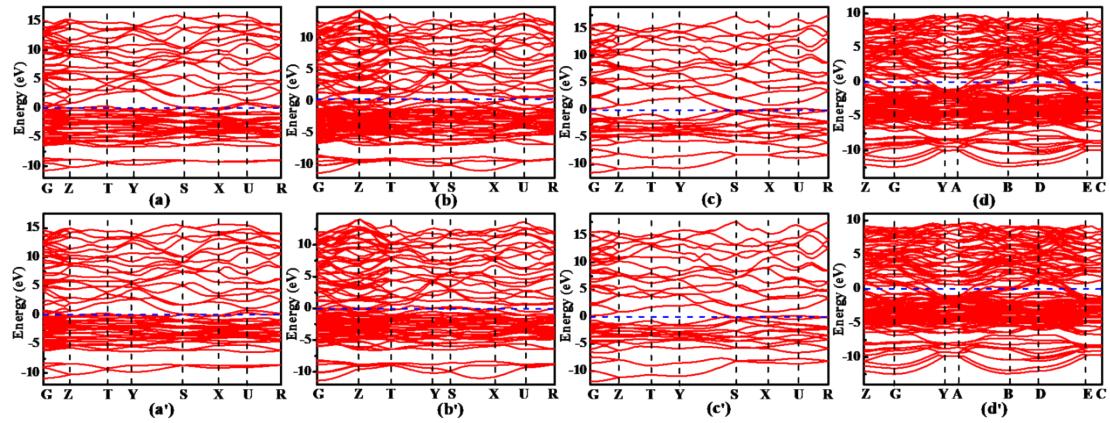


Fig. S4. Calculated band structures of (a) Rh_2Si ($Pnma$), (b) Rh_5Si_3 ($Pbam$), (c) RhSi ($Pnma$), and (d) Rh_4Si_5 ($P2_1/m$) using LDA+U functional, and (a') Rh_2Si ($Pnma$), (b') Rh_5Si_3 ($Pbam$), (c') RhSi ($Pnma$), and (d') Rh_4Si_5 ($P2_1/m$) using GGA-PBE functional, respectively. The Fermi level is at 0 eV.

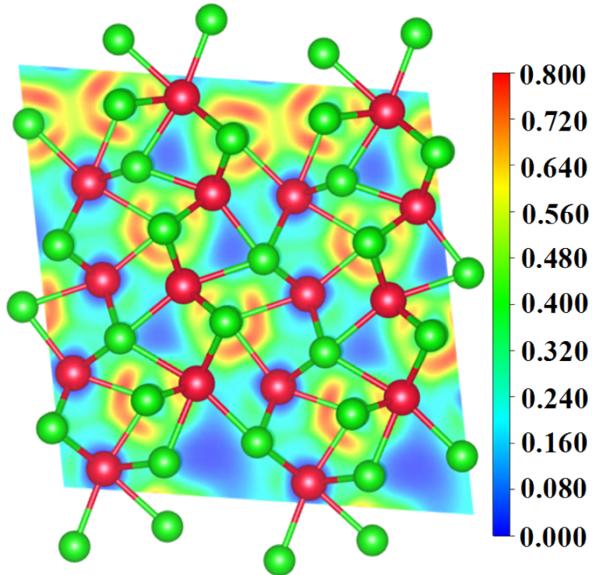


Fig. S5. Electron localization function (ELF) maps projected on to (010) plane of $P2_1/m$ phase Rh_4Si_5 . The ELF isosurfaces value is 0.8.

Table S1. Calculated lattice parameters, a , b , and c (\AA); volume (V in \AA^3) per atom; density (g/cm^3), and relative total energy per chemical formula unit (ΔH in eV) of rhodium silicides with various stoichiometries, compared with experimental and other theoretical data.

Phase	Space group	ΔH	a		b		c		V	ρ	
			Expt.	Theor.	Expt.	Theor.	Expt.	Theor.			
Rh ₃ Si	$C2/m$	–0.55	8.06		7.47		5.49		14.06	9.94	
	$Pnma$	–0.56	5.36		7.99		5.27		14.12	9.90	
	$I4/mcm$	–0.55	5.50		5.50		5.50		14.10	9.92	
	$Pm-3m$	–0.38	3.84		3.84		3.87		14.11	9.91	
Rh ₅ Si ₂	$Fm-3m$	–0.25	6.12		6.12		6.12		14.30	9.77	
	$P4_{1}2_{1}2$	–0.51	9.53		9.53		8.80		14.25	9.50	
	$Pnma$	–0.82	5.58	5.41 ^a	3.99	3.93 ^a	7.40	7.38 ^a	13.72	9.44	
	$I4/mmm$	–0.78	4.01		4.01		5.62		15.02	8.62	
Rh ₂ Si	$P-3m1$	–0.65	4.19		4.19		4.19		13.81	9.37	
	$P6_{3}22$	–0.65	4.18		4.19		5.46		13.82	9.37	
	$P-62m$	–0.11	7.66		7.66		2.81		15.87	8.16	
	$P6_{3}/mmc$	–0.65	4.19		4.19		5.46		13.82	9.37	
Rh ₅ Si ₃	$Pbam$	–0.86	5.45	5.32 ^a	10.32	10.13 ^a	3.90	3.90 ^a	13.72	9.06	
	$P6_{3}/mcm$	–0.44	7.39		7.39		4.99		14.78	8.41	
	$Ia-3d$	–0.44	8.40		8.40		8.40		14.24	8.73	
	$Cmc2_1$	–0.68	13.29		11.43		7.50		14.25	8.50	
RhSi	$P2_1/c$	–0.88	4.63	4.59 ^b	4.62	4.57 ^b	5.64	5.53 ^b	13.66	7.96	
	$Pnma$	–0.91	5.60	5.56 ^b	5.60 ^c	3.11	3.70 ^b	3.11 ^c	6.45	6.38 ^b	
	$P2_{1}3$	–0.88	4.70	4.68 ^b	4.73 ^c	4.73	4.68 ^b	4.73 ^c	4.73	4.68 ^b	
	$Pm-3m$	–0.63	2.90	2.96 ^d	2.90	2.96 ^d	2.99	2.96 ^d		13.34	8.15
Rh ₄ Si ₅	$P2_1/m$	–0.82	12.47		3.55		6.01			14.53	7.01
Rh ₃ Si ₄	$Pnma$	–0.56	20.57		4.45		4.50			14.71	6.79
	$Pbcn$	–0.61	10.58		9.09		6.03			14.50	6.65
Rh ₂ Si ₃	$P-4c2$	–0.56	5.69		5.69		8.99			14.58	6.61
	$P6_{3}/mmc$	–0.62	3.76		3.76		12.52			15.36	6.27
Rh ₃ Si ₅	$P2_1/c$	–0.65	6.48		14.24		11.64			14.99	6.22
	$Cmce$	–0.55	6.98		6.98		8.09			15.46	5.70
RhSi ₂	$P4/mmm$	–0.42	2.93		2.93		5.25			15.08	5.84
	$Fm-3m$	–0.55	5.71		5.71		5.71			15.49	5.68
RhSi ₃	$P6_{3}mc$	–0.03	4.81		4.81		6.36			15.95	4.87
	$P6_{3}/mmc$	–0.02	4.36		4.36		7.44			15.30	5.08

^a Ref. 1, ^b Ref. 2, ^c Ref. 3, ^d Ref. 4.

Table S2. Optimized Structural Parameters for the rhodium silicides.

Structure		Lattice parameters	Atom	Positions(x, y, z)		
				x	y	z
Rh ₃ Si	<i>Pnma</i>	<i>a</i> =10.72, <i>b</i> = 7.99, <i>c</i> =5.27	Rh1(8d)	0.1818	0.0227	0.3143
			Rh2(4c)	0.0007	0.2500	0.9538
			Si1(4c)	0.9441	0.2500	0.4882
Rh ₅ Si ₂	<i>P4₁2₁2</i>	<i>a</i> =9.53, <i>b</i> =9.53, <i>c</i> =8.80	Rh1(8b)	0.4421	0.1687	0.3593
			Rh2(8b)	0.1722	0.2211	0.1710
			Rh3(8b)	0.3886	0.4244	0.1814
			Rh4(8b)	0.3816	0.0292	0.0615
			Rh5(4a)	0.1622	0.1622	0.5000
			Rh6(4a)	0.4291	0.4291	0.5000
			Si1(8b)	0.5016	0.2504	0.0433
Rh ₂ Si	<i>Pnma</i>	<i>a</i> =5.58, <i>b</i> =3.99, <i>c</i> =7.40	Si2(8b)	0.3885	0.2057	0.6187
			Rh1(4c)	0.8433	0.2500	0.0713
			Rh2(4c)	0.9755	0.2500	0.6927
Rh ₅ Si ₃	<i>Pbam</i>	<i>a</i> =5.45, <i>b</i> =10.32, <i>c</i> =3.90	Si1(4c)	0.2735	0.2500	0.1056
			Rh1(2c)	0.0000	0.5000	0.0000
			Rh2(4g)	0.1606	0.2120	0.0000
			Rh3(4h)	0.3330	0.3931	0.5000
			Si1(4h)	0.4082	0.1558	0.5000
Rh ₃ Si ₂	<i>Cmc2₁</i>	<i>a</i> =8.16, <i>b</i> =8.16, <i>c</i> =6.92	Si2(2a)	0.0000	0.0000	0.0000
			Rh1(4)	0.2902	0.0562	0.5180
			Rh2(4)	0.2912	0.0534	0.9000
			Rh3(4)	0.4439	0.0495	0.2170
			Rh4(4)	0.6799	0.3151	0.2250
			Rh5(2)	0.0000	0.0000	0.0000
			Rh6(2)	0.2345	0.2345	0.0240
			Rh7(2)	0.2330	0.2330	0.4000
			Rh8(2)	0.3814	0.3814	0.7140
			Si1(4)	0.1790	0.0610	0.2140
RhSi	<i>Pnma</i>	<i>a</i> =5.60, <i>b</i> =3.11, <i>c</i> =6.45	Si2(4)	0.4860	0.1820	0.5060
			Si3(4)	0.4940	0.1920	0.9200
Rh ₄ Si ₅	<i>P2₁/m</i>	<i>a</i> =12.47, <i>b</i> =3.55, <i>c</i> =6.01	Si4(2)	0.1570	0.1570	0.7120
			Si5(2)	0.4090	0.4090	0.2180
			Rh1(4c)	0.0029	0.2500	0.2032
			Si1(4c)	0.1849	0.2500	0.5561
			Rh1(2e)	0.0499	0.2500	0.2091
			Rh2(2e)	0.2731	0.2500	0.1070
			Rh3(2e)	0.5001	0.2500	0.2994
			Rh4(2e)	0.7308	0.2500	0.2866
			Si1(2e)	0.6350	0.2500	0.6385
			Si2(2e)	0.4221	0.2500	0.8933
Rh ₃ Si ₄	<i>Pnma</i>	<i>a</i> =20.56, <i>b</i> =4.45, <i>c</i> =4.50	Si3(2e)	0.2237	0.2500	0.4649
			Si4(2e)	0.9229	0.2500	0.4876
			Si5(2e)	0.1395	0.7500	0.9790
			Rh1(4c)	0.0486	0.2500	0.5239
			Rh2(4c)	0.2136	0.2500	0.0464
			Rh3(4c)	0.3651	0.2500	0.2606

			Si4(4c)	0.4089	0.7500	0.5137
		$a=3.76, b=3.76, c=12.52$	Rh1(4f)	0.3333	0.6666	0.1391
Rh_2Si_3	$P6_3/mmc$		Si1(4f)	0.3333	0.6666	0.9423
			Si2(2b)	0.0000	0.0000	0.2500
			Rh1(4e)	6.4780	14.2392	11.635
			Rh2(4e)	0.5642	0.5944	0.3961
			Rh3(4e)	0.9517	0.7525	0.2446
			Rh4(4e)	0.0833	0.9553	0.2722
			Rh5(4e)	0.2297	0.6667	0.1321
			Rh6(4e)	0.2334	0.8345	0.9940
			Si1(4e)	0.9279	0.8433	0.0692
Rh_3Si_5	$P2_1/c$	$a=6.47, b=14.24, c=11.64$	Si2(4e)	0.7456	0.4890	0.5759
			Si3(4e)	0.8648	0.6104	0.3292
			Si4(4e)	0.3289	0.9433	0.1648
			Si5(4e)	0.8565	0.6123	0.1087
			Si6(4e)	0.3519	0.9355	0.5086
			Si7(4e)	0.9495	0.6481	0.9068
			Si8(4e)	0.2547	0.9879	0.7050
			Si9(4e)	0.3770	0.7504	0.8548
			Si10(4e)	0.5524	0.7777	0.1965
RhSi_2	$Cmce$	$a=11.41, b=8.05, c=8.09$	Rh1(8d)	0.2501	0.0000	0.5000
			Rh2(8f)	0.5000	-0.2464	0.2534
			Si1(16g)	0.1248	-0.2498	0.4977
			Si2(16g)	0.3745	0.0025	0.2499
RhSi_3	$P6_3mc$	$a=4.81, b=4.81, c=6.36$	Rh1(2b)	0.3333	0.6666	0.2522
			Si1(6c)	0.8333	0.1666	0.0822

Table S3. Calculated (at GGA and LDA levels) and experimental lattice parameters, a , b , and c ; volume V per atom, density, and relative total energy per chemical formula unit ΔH of rhodium silicides with various stoichiometries.

Phase	Space	method	ΔH (eV)	a (Å)	b (Å)	c (Å)	V (Å 3)	ρ (g/cm 3)
Rh ₂ Si	<i>Pnma</i>	GGA	-0.82	5.58	3.99	7.40	13.72	9.44
		LDA+U	-0.82	5.63	3.97	7.32	13.62	9.50
		Expt.		5.41 ^a	7.38 ^a	7.38 ^a		
Rh ₅ Si ₃	<i>Pbam</i>	GGA	-0.86	5.45	10.32	3.90	13.72	9.06
		LDA+U	-0.88	5.47	10.26	3.88	13.61	9.13
		Expt.		5.32 ^a	10.13 ^a	3.90 ^a		
RhSi	<i>Pnma</i>	GGA	-0.91	5.60	3.11	6.45	14.05	7.74
		LDA+U	-0.91	5.62	3.12	6.49	14.22	7.65
		Expt.		5.56 ^b	3.70 ^b	6.38 ^b		
Rh ₄ Si ₅	<i>P2₁/m</i>	GGA	-0.82	12.47	3.55	6.01	14.53	7.01
		LDA+U	-0.86	12.45	3.55	5.98	14.44	7.05

^a Ref. 1, ^b Ref. 2,

Table S4. Calculated bond length d^μ , Mulliken overlap population P^μ , f_m , bond volume, and Vickers hardness H_v (GPa) for rhodium silicides with different structures.

Structure	Band	$d^\mu(\text{\AA})$	P^μ	f_m	$v_b^\mu(\text{\AA}^3)$	H_v^μ	H_v
Rh_2Si <i>(Pnma)</i>	Si-Rh	2.415	0.130	0.321	3.812	7.026	11.9
		2.423	0.370	0.113	3.851	25.676	
		2.471	0.415	0.100	4.086	26.458	
		2.480	0.300	0.139	4.127	18.002	
		2.520	0.340	0.123	4.331	19.186	
		2.851	0.110	0.379	6.271	2.370	
Rh_5Si_3 <i>(Pbam)</i>	Si-Rh	2.357	0.150	0.099	3.241	14.090	12.0
		2.369	0.130	0.114	3.292	11.697	
		2.420	0.425	0.035	3.508	37.476	
		2.443	0.370	0.040	3.608	30.962	
		2.483	0.340	0.044	3.792	26.096	
		2.577	0.360	0.041	4.239	23.003	
RhSi <i>(Pnma)</i>	Si-Rh	2.725	0.040	0.371	5.009	1.269	
		2.750	0.105	0.141	5.150	4.344	
		2.437	0.310	0.003	4.270	20.346	14.7, 14.8 ^a
		2.444	0.350	0.003	4.306	22.655	
		2.526	0.225	0.005	4.756	12.323	
		2.691	0.260	0.004	5.749	10.387	
Rh_4Si_5 <i>(P2₁/m)</i>	Si-Rh	2.324	0.435	0.002	3.943	32.657	20.1
		2.338	0.010	0.071	3.943	0.698	
		2.400	0.410	0.002	3.943	30.777	
		2.411	0.420	0.002	3.943	31.529	
		2.428	0.220	0.003	3.943	16.490	
		2.437	0.330	0.002	3.943	24.761	
		2.438	0.350	0.002	3.943	26.265	
		2.462	0.435	0.002	3.943	32.657	
		2.463	0.095	0.007	3.943	7.090	
		2.485	0.365	0.002	3.943	27.393	
		2.486	0.260	0.003	3.943	19.498	
		2.499	0.040	0.018	3.943	2.954	
		2.520	0.395	0.002	3.943	29.649	
		2.526	0.275	0.003	3.943	20.625	
		2.612	0.385	0.002	3.943	28.897	
		2.687	0.370	0.002	3.943	27.769	
Si-Si	Si-Si	2.774	0.235	0.003	3.943	17.618	
		2.779	0.250	0.003	3.943	18.746	
		2.596	0.360	0.002	3.943	27.017	
		2.601	0.400	0.002	3.943	30.025	
		2.651	0.295	0.002	3.943	22.129	
		Si (<i>Fd-3m</i>)	Si-Si	2.374	0.730	0.001	10.297 11.074 11.1

^a Ref.3

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